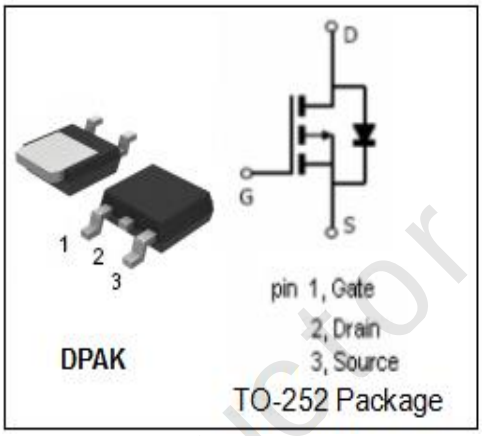
JSMD409
P-Channel MOSFET Transistor

- **FEATURES**
- TO-252(DPAK) packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



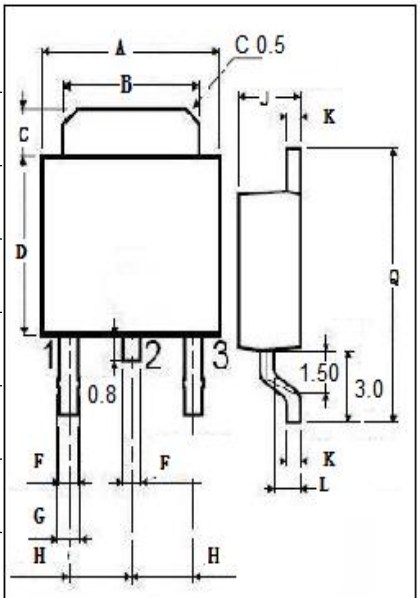
- **APPLICATIONS**
- Power supply
- Switching applications

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-60	V
V_{GSS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous@T_C=25℃ T_C=100℃	-26 -18	A
I_{DM}	Drain Current-Single Pulsed	-60	A
P_D	Total Dissipation	60	W
T_j	Operating Junction Temperature	175	℃
T_{stg}	Storage Temperature	-55~175	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	2.5	℃/W
Rth(ch-a)	Channel-to-ambient thermal resistance	50	℃/W



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= -0.25mA	-60			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=-0.25mA	-1.2		-2.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -10V; I_D=-20A		32	40	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0V			±0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= -48V; V_{GS}= 0V;Tj=25℃ Tj=55℃			-1 -5	μA
V_{SDF}	Diode forward voltage	I_{SD}=-1A, V_{GS} = 0 V			-1	V